**To make a MASK**

**Photolithography exposure wizard**

Size XY 10053/2005.7 um

Offset -996.5 / 177.5 um

12mW

Energy mode 1/1

Positive mask - uncheck inverted

(Orientation 5000 um in y direction)

Size XY 10053/2005.7 um

Offset -996.5 / 177.5 um

1257 stripes

Gdsii. 1257 stripes.

**Exposure for mask**

AZ developer 1:1

Develop for 1 min, the run under rinse water

DI rinse - hit run

Dip for 3.5 min in Cr 14-S chromium etch

Rinse in DI for 2 min

Run in spin dryer (put in last spot)

**Spin resist**

S1813 - glue photoresist - 1 min

* 3 drops on the center of the wafer
* 2000 rpms, 5 seconds

AZ 9260- chip photoresist - 3min

* Enough to cover the chip
* 3000 rpms, 60 seconds

**Development/After UV exposure**

1) 150ml water + 50ml of 400K in a bowl and then rinse the beaker 3 times with water

2) place the wafer in the bowl for 6mins

3) water rinse and dry with nitrogen spray

4) aspirated the solution in the bowl